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Electrical ratings 1

Table 1. **Absolute maximum ratings**

Symbol	Parameter		Unit					
V _{DS}	Drain-source voltage (V _{GS} = 0)		V					
V _{GS}	Gate-source voltage		clamped		V			
I _D	Drain current (continuous) at T _C = 25°C		80		Α			
I _D	Drain current (continuous) at T _C = 100°C		60		Α			
I _{DG}	Drain gate current (continuous)		± 50		mA			
I _{GS}	Gate source current (continuous)	± 50			mA			
I _{DM} ⁽¹⁾	Drain current (pulsed)	320			Α			
P _{TOT}	Total dissipation at T _C = 25°C	dissipation at T _C = 25°C 300			W			
	Derating factor	2.0			W/°C			
V _{ESD(G-S)}	Gate-source ESD(HBM-C=100 pF, R=1.5 $\mathrm{K}\Omega$)		4	NCr	KV			
T _J T _{stg}	Operating junction temperature Storage temperature		-55 to 175		°C			
Pulse width limited by safe operating area Table 2. Thermal data								
	O	TO-220	D ² PAK/I ² PA	TO-247	Unit			

^{1.} Pulse width limited by safe operating area

Table 2. Thermal data

		TO-220	D ² PAK/I ² PA K	TO-247	Unit
R _{thj-case}	Thermal resistance junction-case Max	0.50			°C/W
Rthj-pcb ⁽¹⁾	Thermal resistance junction-pcb Max	35			°C/W
R _{thj-a}	Thermal resistance junction-ambient Max	62.5		50	
T ₁ (2)	Maximum lead temperature for soldering purpose	300			°C

When mounted on 1 inch² FR4 2oZ Cu

Table 3. **Avalanche characteristics**

Symbol	Parameter	Value	Unit
I _{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by Tj Max)	80	А
E _{AS}	Single pulse avalanche energy (starting Tj=25°C, Id=lar, Vdd=30V)	500	mJ

^{(1.6} mm from case, for 10 sec)

Electrical characteristics 2

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0 -40 < Tj < 175 °C	33			٧
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	$V_{DS} = 16 \text{ V,T}_j = 25 \text{ °C}$ $V_{DS} = 16 \text{ V,T}_j = 125 \text{ °C}$			10 100	μ Α μ Α
I _{GSS}	Gate body leakage current (V _{DS} = 0)	$V_{GS} = \pm 10 \text{ V},$ $T_{j} = 25 \text{ °C}$			10	nA
V _{GSS}	Gate-source breakdown voltage	I _{GS} = ± 100μA	18			٧
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS} = I_D = 1 \text{ mA}$	2		4	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V ,I _D = 40 A		7)	9	mΩ

Dynamic Table 5.

	Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
	g _{fs} ⁽¹⁾	Forward transconductance	$V_{DS} = 15V, I_D = 40A$		50		S
	C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} =25V, f=1 MHz, V _{GS} =0		2700 1275 285		pF pF pF
	t _{d(on)} t _r	Turn-on delay time Rise time	$V_{DD} = 17.5 \text{ V}, I_{D} = 40 \text{ A},$ $R_{G} = 4.7 \Omega, V_{GS} = 10 \text{ V}$ (see Figure 13)		40 10		ns ns
	t _{d(off)}	Turn-off delay time Fall time	$V_{DD} = 17.5 \text{ V}, I_D = 40 \text{ A},$ $R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$ (see Figure 13)		220 100		ns ns
105018	Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} =20V, I_{D} = 80A V_{GS} =10V (see Figure 14)		80 20 27	105	nC nC nC
Oh	1. Pulsed: ¡	oulse duration=300μs, duty cycle	1.5%				

^{1.} Pulsed: pulse duration=300µs, duty cycle 1.5%

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I _{SD}	Source-drain current				80	Α
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)				320	Α
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} =80A, V _{GS} =0			1.5	٧
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} =80A, di/dt = 100A/ μ s, V_{DD} =25V, Tj=150°C (see Figure 15)		90 0.18 4		ns μC A

- 1. Pulse width limited by safe operating area
- 2. Pulsed: pulse duration=300µs, duty cycle 1.5%

 Obsolete Product(S)

 Obsolete Product(S)

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

Figure 2. Thermal impedance

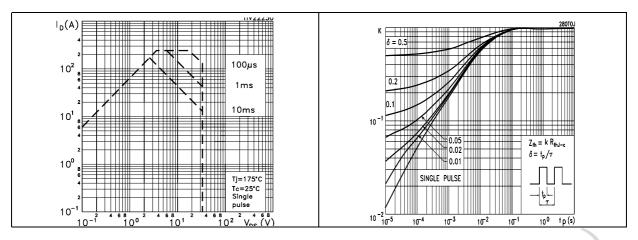


Figure 3. Output characterisics

Figure 4. Transfer characteristics

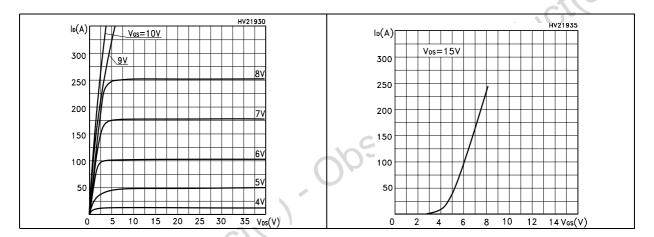


Figure 5. Transconductance

Figure 6. Static drain-source on resistance

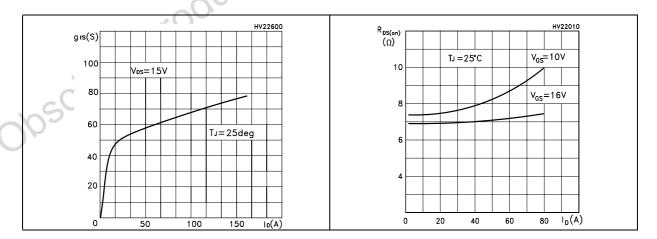


Figure 7. Gate charge vs gate-source voltage Figure 8. Normalized on resistance vs temperature

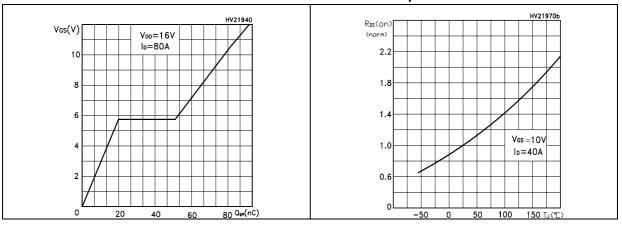


Figure 9. Normalized gate threshold voltage Figure 10. Source-drain diode forward vs temperature characteristics

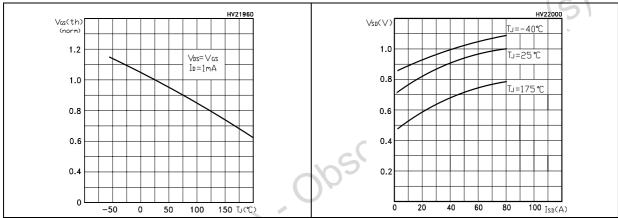
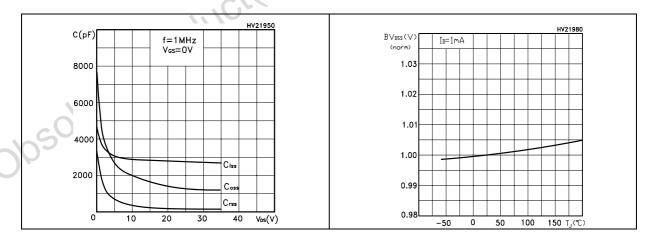


Figure 11. Capacitance variations

Figure 12. Normalized B_{VDSS} vs temperature



Test circuit 3

Figure 13. Switching times test circuit for resistive load

Figure 14. Gate charge test circuit

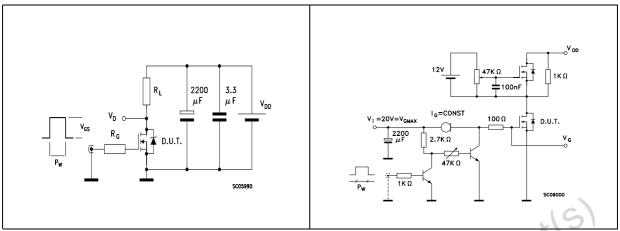


Figure 15. Test circuit for inductive load switching and diode recovery times

Figure 16. Unclamped Inductive load test circuit

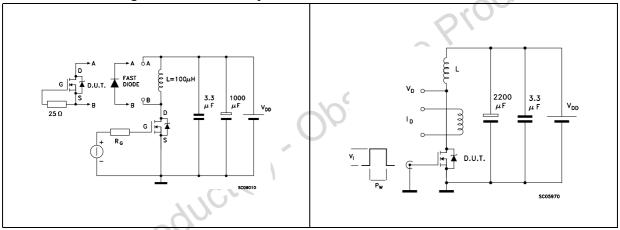
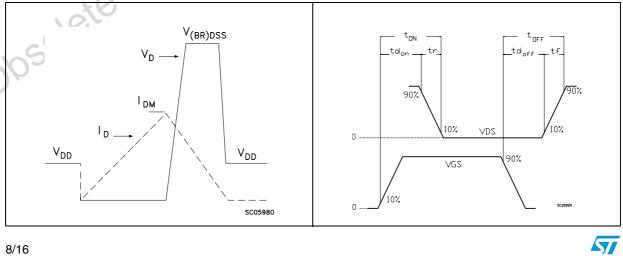


Figure 17. Unclamped inductive waveform

Figure 18. Switching time waveform



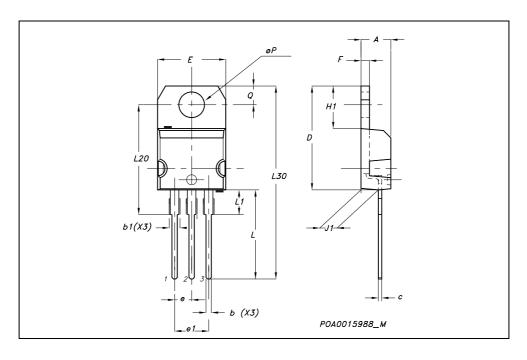
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Product(s). Obsolete Product(s)

TO-220 MECHANICAL DATA

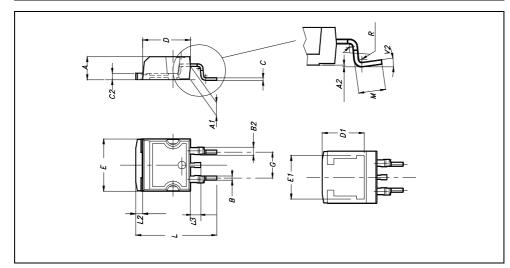
DIM.		mm.			inch	
DIN.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øΡ	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



Obsole

D²PAK MECHANICAL DATA

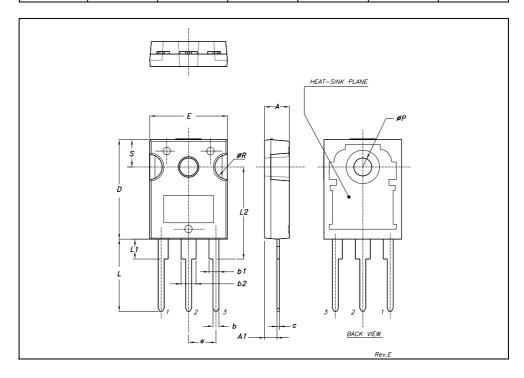
DIM.		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
Е	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	Oº		4º			



Obsole

TO-247 MECHANICAL DATA

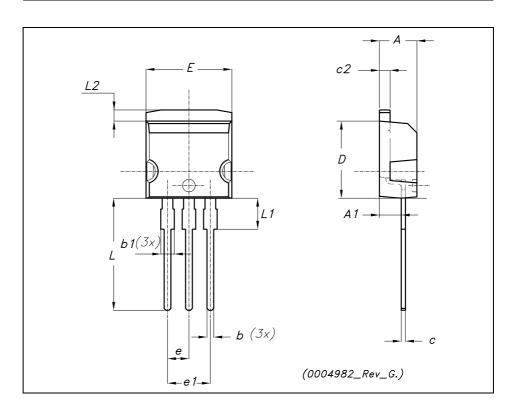
DIM.		mm.			inch	
DIIVI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
С	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
Е	15.45		15.75	0.608		0.620
е		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øΡ	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



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TO-262 (I²PAK) MECHANICAL DATA

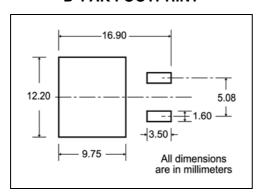
DIM	mm.				inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



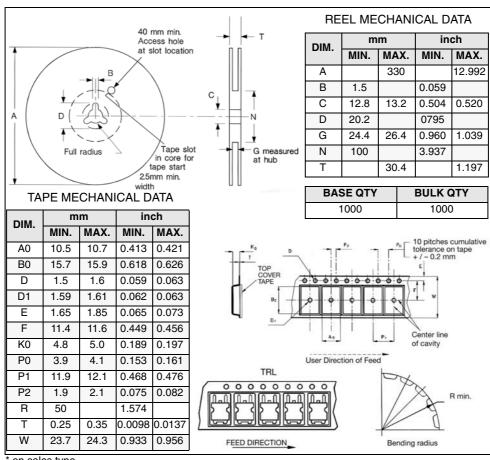
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Packaging mechanical data 5

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT







6 Revision history

Table 7. Revision history

Date	Revision	Changes
10-Feb-2005	1	First release.
14-Jan-2006	2	Inserted D ² PAK, complete version.
03-Oct-2006	3	Inserted I ² PAK.



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